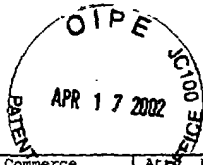


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	4,389,973	28-Jun-1983	Apparatus For Performing Growth of Compound Thin Films			11-Dec-1983
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	5,130,269	14-Jul-1992	Hetero-epitaxially grown compound semiconductor substrate and a method of growing the same			25-Apr-1989
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	5,338,389	16-Aug-1994	Method of epitaxially growing compound crystal and doping method therein			21-Apr-1993
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	5,395,791	7-Mar-1995	Growth of II VI laser diodes with quantum wells by atomic layer epitaxy and migration enhanced epitaxy			20-Oct-1993
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	5,705,224	6-Jan-1998	Vapor Depositing Method			31-Jan-1995
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	5,851,849	22-Dec-1998	Process for Passivating Semiconductor Laser Structures with Severe Steps in Surface Topography			22-May-1997
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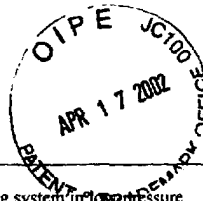
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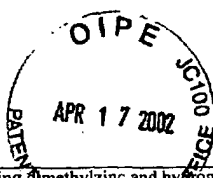
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